

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
-20V	44mΩ @ V _{GS} = -4.5V	-4.6A
	57mΩ @ V _{GS} = -2.5V	-4A
	74mΩ @ V _{GS} = -1.8V	-3.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Load Switch

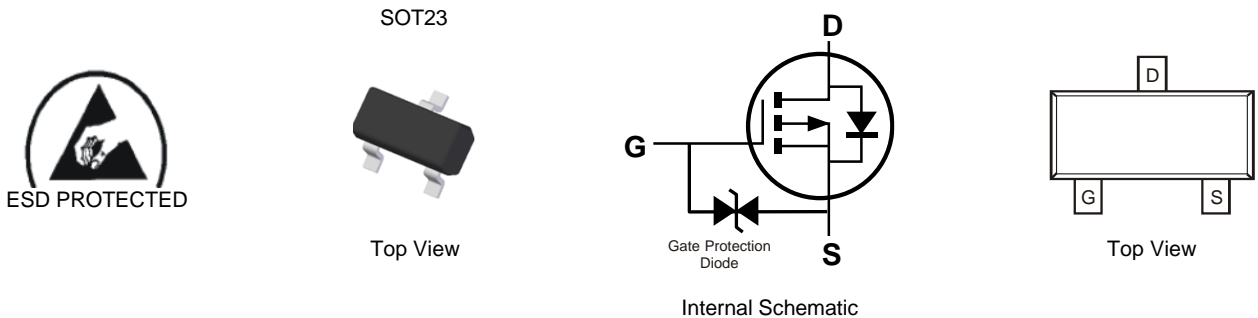
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMP2070UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

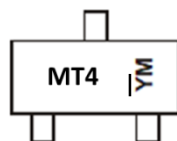


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2070UQ-7	SOT23	3,000 / Tape & Reel
DMP2070UQ-13	SOT23	10,000 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



MT4 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: H = 2020)
 M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	H	I	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 7) V _{GS} = -4.5V	I _D	T _C = +25°C	-4.6
		T _C = +70°C	-3.7
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	-20	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-1.9	A
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	-14	A
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	10	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	0.83	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	153	°C/W
Total Power Dissipation (Note 6)	P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	90	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	15.1	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-0.45	—	-0.95	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	37	44	mΩ	V _{GS} = -4.5V, I _D = -2A
		—	48	57		V _{GS} = -2.5V, I _D = -2A
		—	65	74		V _{GS} = -1.8V, I _D = -2A
		—	—	—		V _{GS} = 0V, I _S = -2.1A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.1	V	V _{GS} = 0V, I _S = -2.1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	118	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	79	—		
Reverse Transfer Capacitance	C _{rss}	—	11	—		
Gate Resistance	R _G	—	459	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -8V)	Q _g	—	8.2	—	nC	V _{DD} = -10V, I _D = -2A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	17.8	—		
Gate-Source Charge	Q _{gs}	—	1.4	—		
Gate-Drain Charge	Q _{gd}	—	1.2	—		
Turn-On Delay Time	t _{D(ON)}	—	115	—	ns	V _{GS} = -4.5V, V _{DD} = -10V, R _G = 1Ω, I _D = -2A
Turn-On Rise Time	t _R	—	304	—		
Turn-Off Delay Time	t _{D(OFF)}	—	780	—		
Turn-Off Fall Time	t _F	—	666	—		
Reverse Recovery Time	t _{RR}	—	—	—	ns	I _F = -2A, di/dt = -100A/μs
Reverse Recovery Charge	Q _{RR}	—	—	—	nC	I _F = -2A, di/dt = -100A/μs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

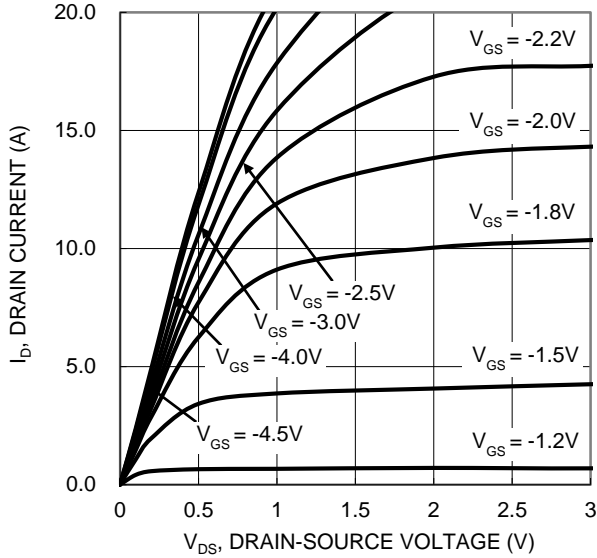


Figure 1. Typical Output Characteristic

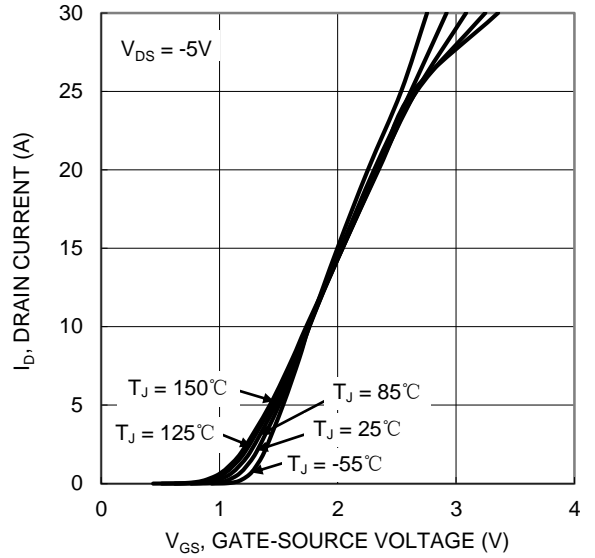


Figure 2. Typical Transfer Characteristic

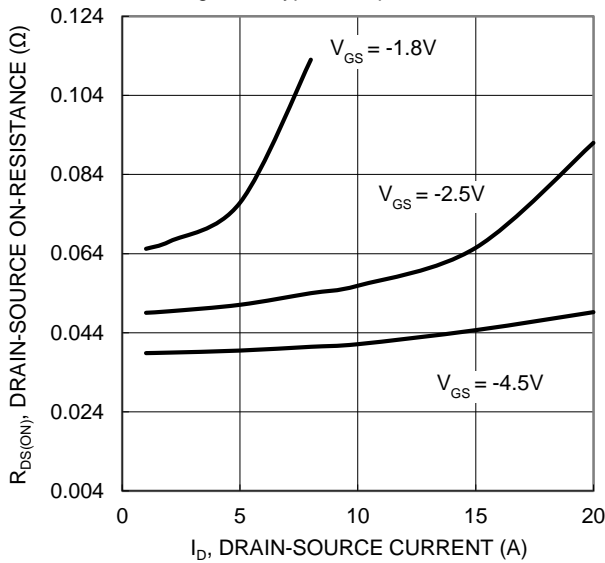


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

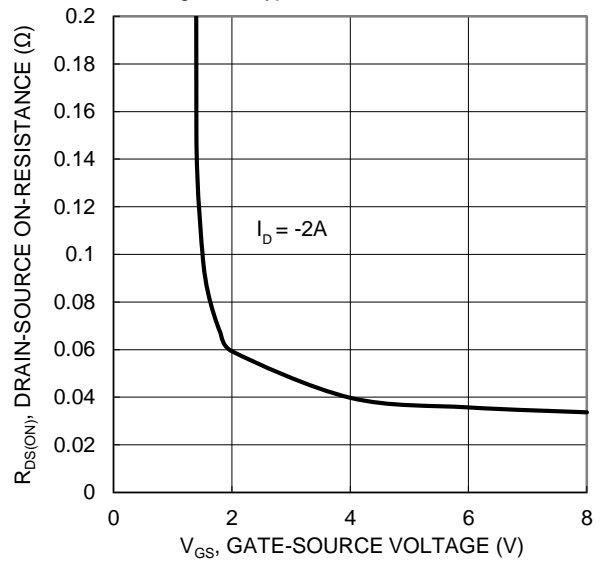


Figure 4. Typical Transfer Characteristic

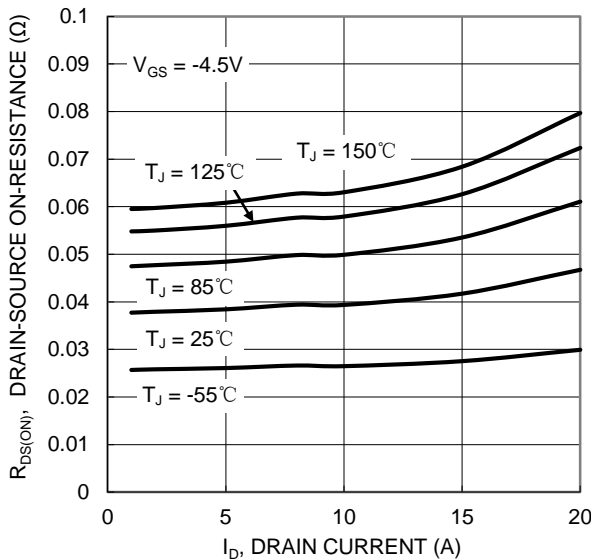


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

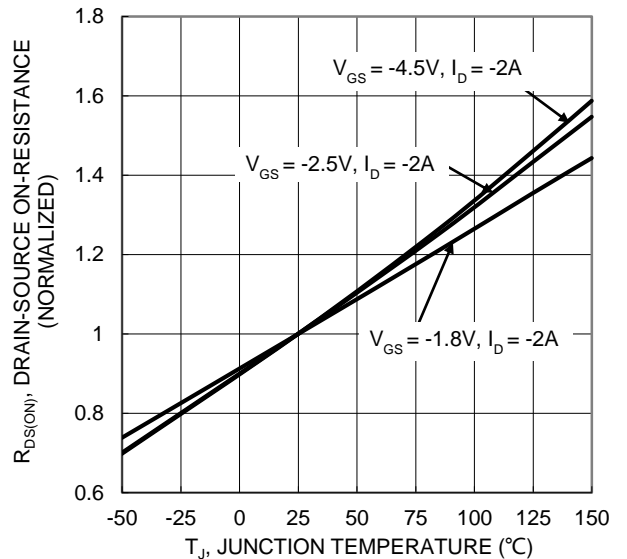


Figure 6. On-Resistance Variation with Junction Temperature

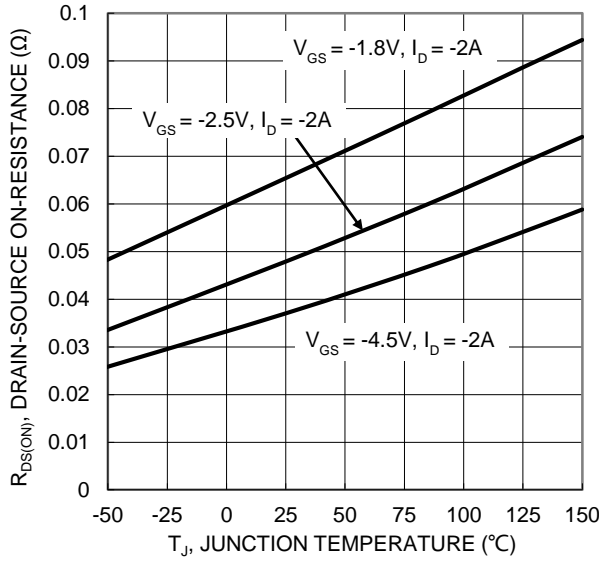


Figure 7. On-Resistance Variation with Junction Temperature

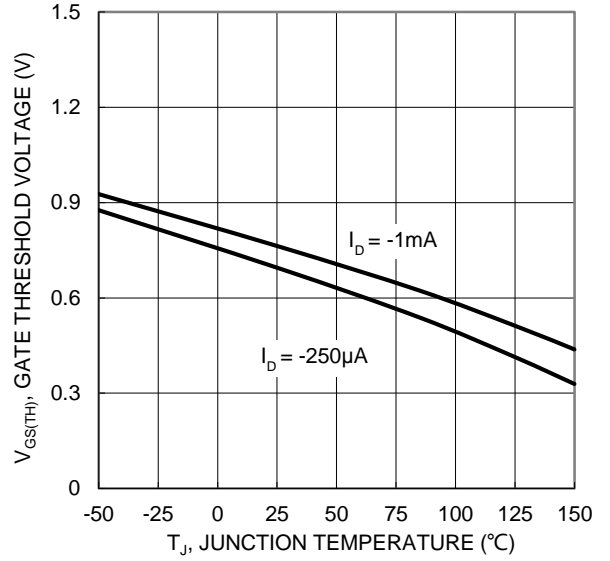


Figure 8. Gate Threshold Variation vs. Junction Temperature

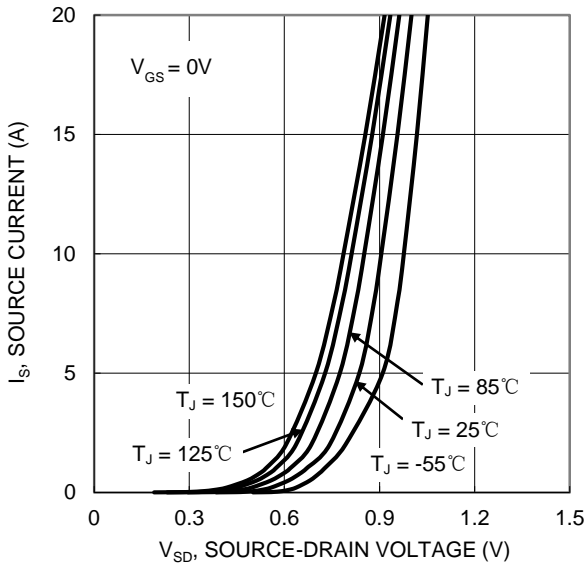


Figure 9. Diode Forward Voltage vs. Current

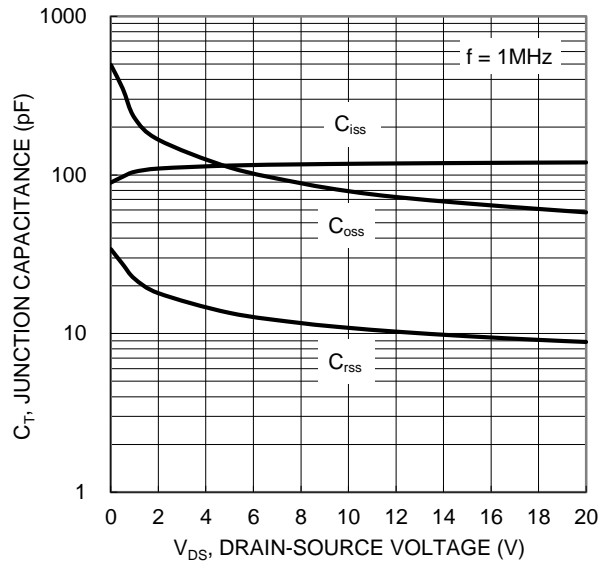


Figure 10. Typical Junction Capacitance

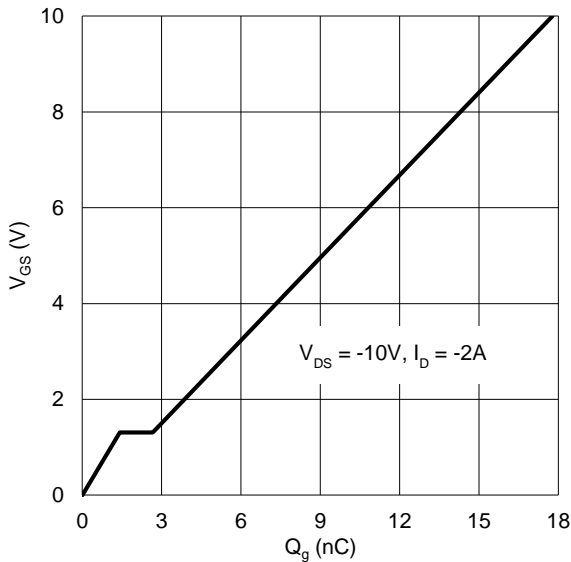


Figure 11. Gate Charge

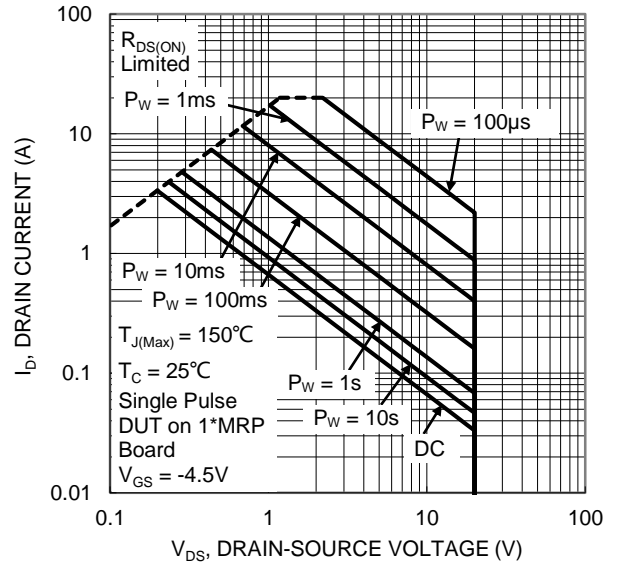


Figure 12. SOA, Safe Operation Area

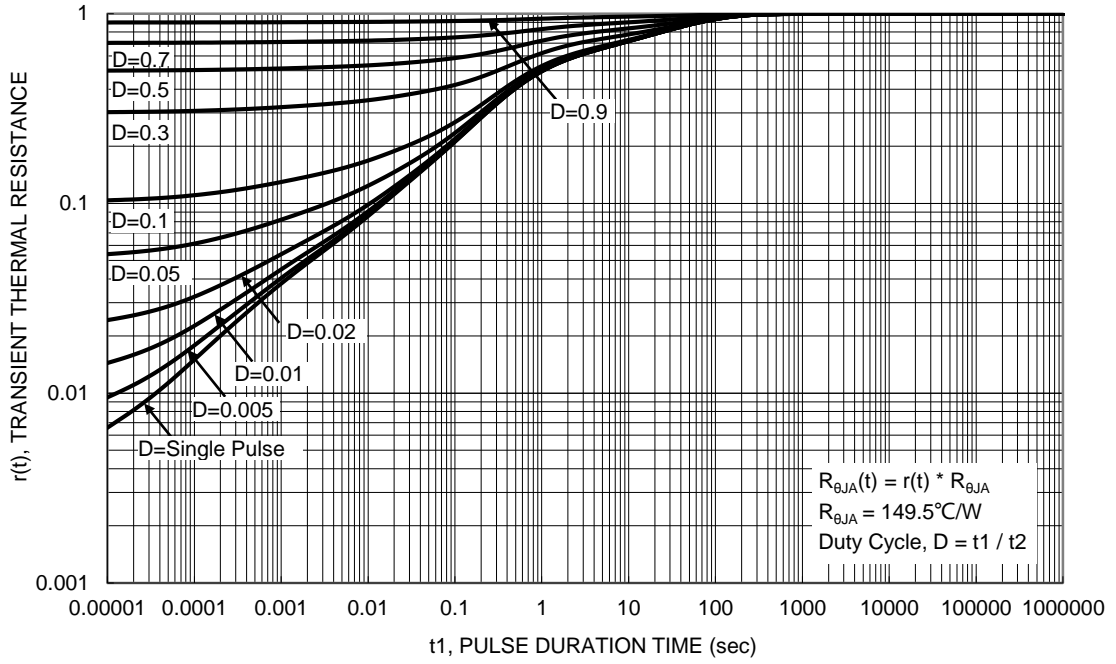
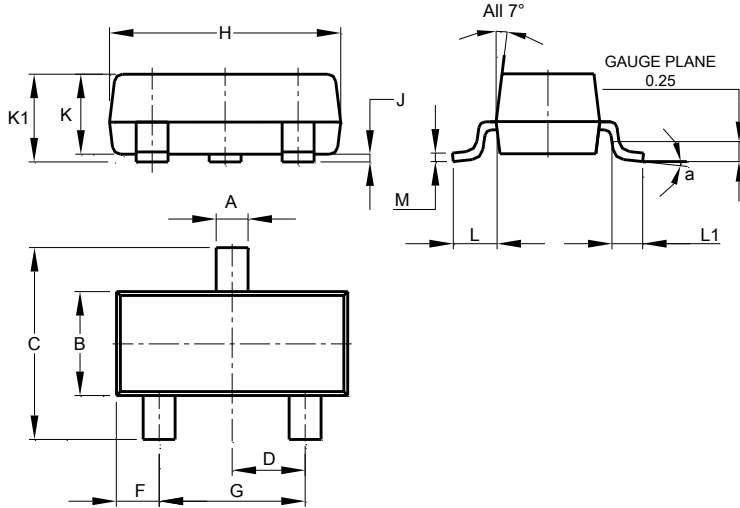


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

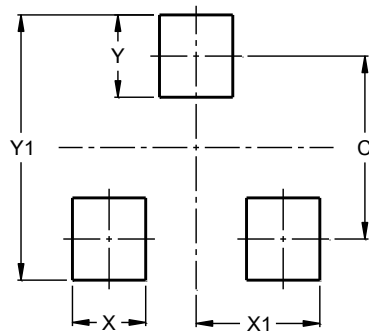


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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